

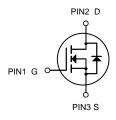
## **Description**

The HXY3400MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

# D G SOT23-3L

#### **General Features**

 $V_{DS} = 30V, I_D = 5.8A$   $R_{DS(ON)} < 28m\Omega$  @  $V_{GS} = 10V$   $R_{DS(ON)} < 34m\Omega$  @  $V_{GS} = 4.5V$ 



## **Application**

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management

N-Channel MOSFET

### **Package Marking and Ordering Information**

| Product ID | Pack     | Marking | Qty(PCS) |
|------------|----------|---------|----------|
| HXY3400MI  | SOT23-3L | X0VX    | 3000PCS  |

#### Absolute Maximum Ratings (T<sub>A</sub>=25℃ unless otherwise noted)

| Symbol                           | Parameter  | Limit      | Unit       |
|----------------------------------|--|------------|------------|
| V <sub>DS</sub>                  | Drain-Source Voltage                             | 30         | V          |
| V <sub>G</sub> s                 | Gate-Source Voltage                              | ±12        | V          |
| Ι <sub>D</sub>                   | Drain Current-Continuous                         | 5.8        | Α          |
| Ідм                              | Drain Current-Pulsed (Note 1)                    | 30         | А          |
| P□                               | Maximum Power Dissipation                        | 1.4        | W          |
| T <sub>J</sub> ,T <sub>STG</sub> | Operating Junction and Storage Temperature Range | -55 To 150 | $^{\circ}$ |
| Reja                             | Thermal Resistance, Junction-to-Ambient (Note 2) | 89         | °C/W       |



# Electrical Characteristics (T<sub>A</sub>=25 <sup>°</sup>C unless otherwise noted)

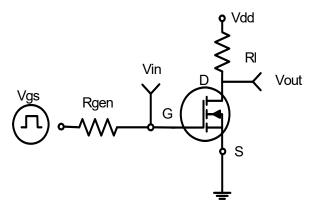
| Parameter                        | Symbol            | Condition                                  | Min | Тур | Max  | Unit |
|----------------------------------|-------------------|--|-----|-----|------|------|
| Off Characteristics              | ,                 |  | "   |     |      |      |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub> | V <sub>GS</sub> =0V I <sub>D</sub> =250µA  | 30  | 33  | -    | V    |
| Zero Gate Voltage Drain Current  | Inss              | $V_{DS}$ =30V, $V_{GS}$ =0V                | -   | -   | 1    | μA   |
| Gate-Body Leakage Current        | Igss              | V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V  | -   | -   | ±100 | nA   |
| Gate Threshold Voltage           | VGS(th)           | $V_{DS}$ = $V_{GS}$ , $I_D$ =250 $\mu$ A   | 0.7 | 0.9 | 1.4  | V    |
|                                  | Rds(on)           | V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A  | -   | 41  | 55   | mΩ   |
| Drain-Source On-State Resistance |                   | V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A  | -   | 23  | 34   | mΩ   |
|                                  |                   | V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A | -   | 21  | 28   | mΩ   |
| Forward Transconductance         | grs               | V <sub>DS</sub> =5V,I <sub>D</sub> =5A     | 10  | -   | -    | S    |
| Input Capacitance                | C <sub>lss</sub>  | V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,  | -   | 825 | -    | PF   |
| Output Capacitance               | Coss              |  | -   | 100 | -    | PF   |
| Reverse Transfer Capacitance     | C <sub>rss</sub>  | F=1.0MHz                                   | -   | 78  | -    | PF   |
| Turn-on Delay Time               | td(on)            |  | -   | 3.3 | -    | nS   |
| Turn-on Rise Time                | tr                | V <sub>DD</sub> =15V, R <sub>L</sub> =2.7Ω | -   | 4.8 | -    | nS   |
| Turn-Off Delay Time              | td(off)           | $V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$   | -   | 26  | -    | nS   |
| Turn-Off Fall Time               | t <sub>f</sub>    |  | -   | 4   | -    | nS   |
| Total Gate Charge                | Qg                |  | -   | 10  | -    | nC   |
| Gate-Source Charge               | Q <sub>gs</sub>   | V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A, | -   | 1.6 | -    | nC   |
| Gate-Drain Charge                | Q <sub>gd</sub>   | V <sub>GS</sub> =4.5V                      | -   | 3.1 | -    | nC   |
| Diode Forward Voltage (Note 3)   | VsD               | V <sub>GS</sub> =0V,I <sub>S</sub> =5.8A   | -   | -   | 1.2  | V    |
| Diode Forward Current (Note 2)   | Is                |  | -   | -   | 5.8  | Α    |

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

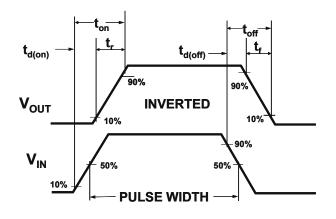
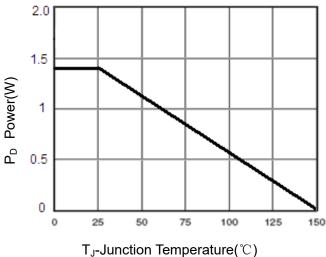
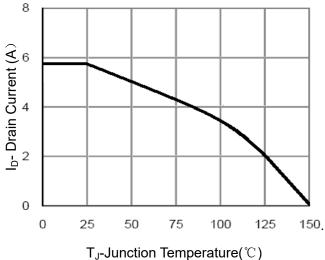


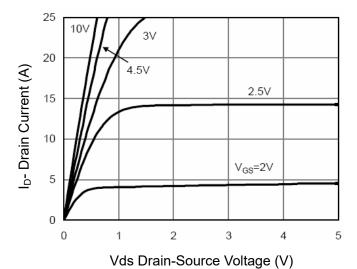
Figure 2:Switching Waveforms





**Figure 4 Drain Current** 





**Figure 5 Output Characteristics** 

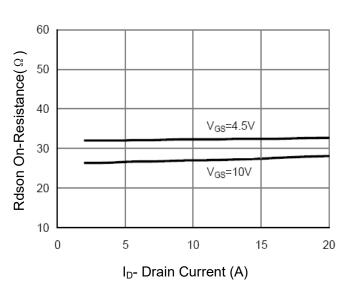
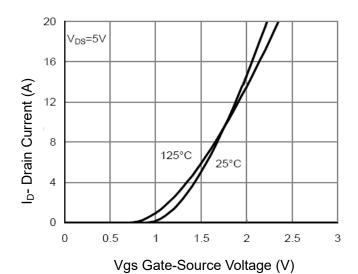


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 

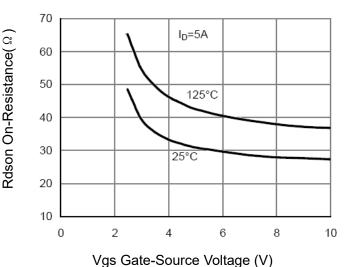
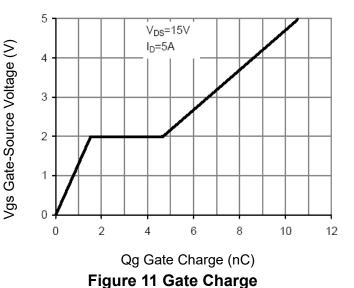


Figure 9 Rdson vs Vgs



1.8 Normalized On-Resistance 1.6 V<sub>GS</sub>=4.5V 1.4 V<sub>GS</sub>=10V 1.2 1 8.0 75 0 25 50 100 125 150 175

Figure 8 Drain-Source On-Resistance

T<sub>J</sub>-Junction Temperature(°C)

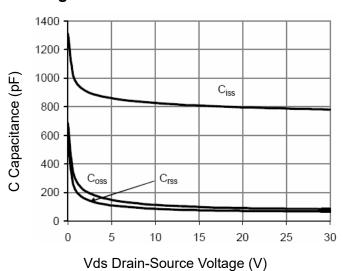


Figure 10 Capacitance vs Vds

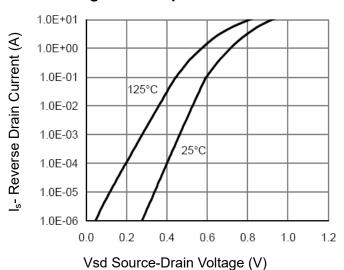


Figure 12 Source- Drain Diode Forward



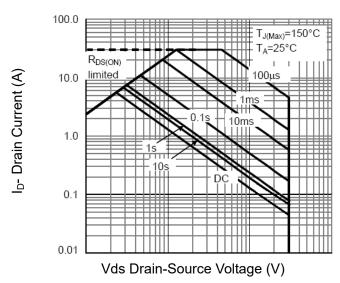
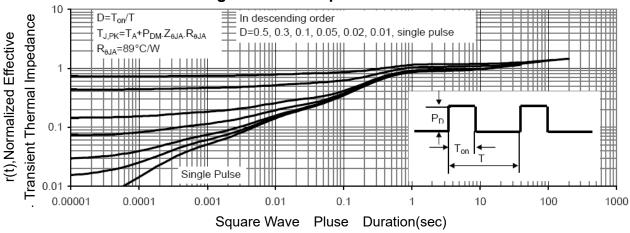
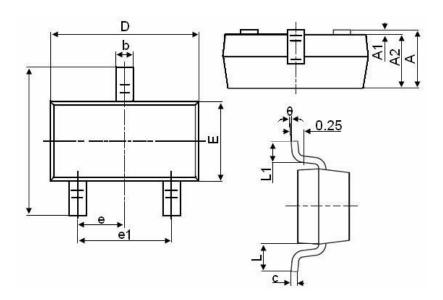


Figure 13 Safe Operation Area



**Figure 14 Normalized Maximum Transient Thermal Impedance** 

# **SOT23-3L Package Information**



| Symbol | Dimensions in Millimeters |          |  |  |
|--------|---------------------------|----------|--|--|
|        | MIN.                      | MAX.     |  |  |
| А      | 1.050                     | 1.250    |  |  |
| A1     | 0.000                     | 0.100    |  |  |
| A2     | 1.050                     | 1.150    |  |  |
| b      | 0.300                     | 0.500    |  |  |
| С      | 0.100                     | 0.200    |  |  |
| D      | 2.800                     | 3.000    |  |  |
| E      | 1.500                     | 1.700    |  |  |
| E1     | 2.650                     | 2.950    |  |  |
| е      |                           | 0.950TYP |  |  |
| e1     | 1.800                     | 2.000    |  |  |
| L      |                           | 0.550REF |  |  |
| L1     | 0.300                     | 0.600    |  |  |
| θ      | 0°                        | 8°       |  |  |



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